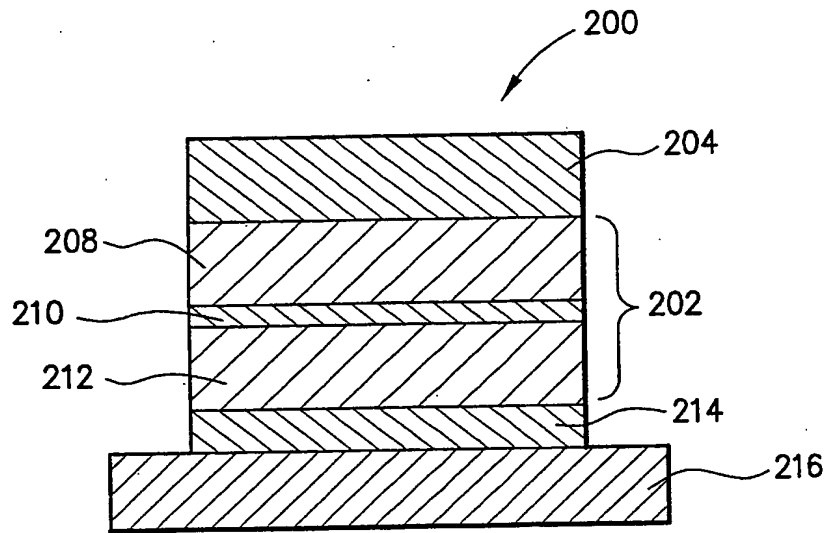
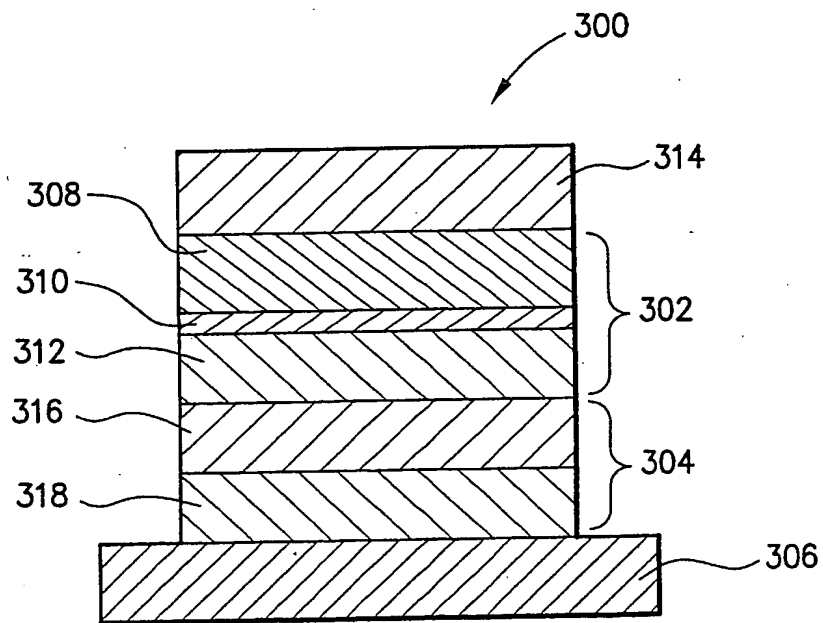
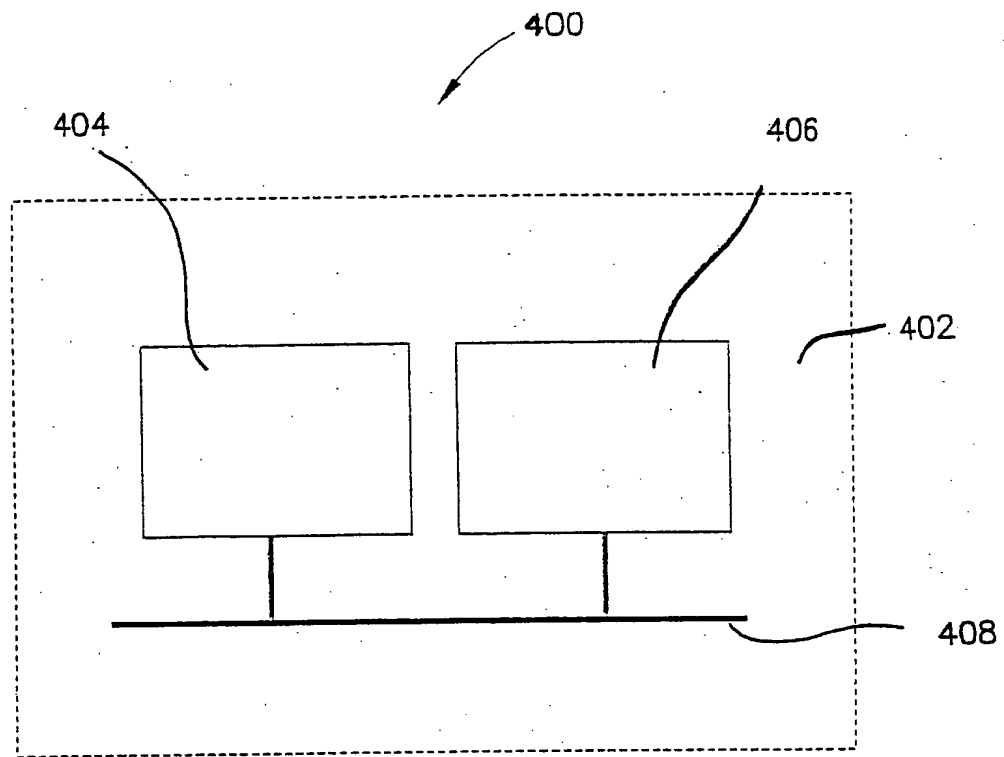
**Fig. 1**



**Fig. 2**



**Fig. 3**



**Fig. 4**

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HEATING MRAM CELLS OF AN ARRAY OF MRAM CELLS SWITCHABLE BETWEEN TWO STATES UNDER THE INFLUENCE OF A MAGNETIC FIELD, EACH MRAM CELL COMPRISING A REFERENCE LAYER AND A DATA LAYER, THE REFERENCE LAYER HAVING A LOWER COERCIVITY THAN THE DATA LAYER

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UTILIZING THE GENERATED HEAT TO REDUCE THE COERCIVITY OF THE REFERENCE LAYER AND FACILITATE SWITCHING OF THE REFERENCE LAYER

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**Fig. 5**